Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection: 2 kV HBM
- Leadless ultra small package: 1.0 × 0.6 × 0.48 mm

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	1.4	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 1.4 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	210	250	mΩ

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D I
2	S	source	2 3	
3	D	drain	Transparent top view DFN1006-3 (SOT883)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMZ200UNE	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMZ200UNE	ZV

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	1.4	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	0.9	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	350	mW
			[1]	-	760	mW
		T _{sp} = 25 °C		-	6250	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain o	liode		,			,
Is	source current	T _{amb} = 25 °C	[1]	-	0.7	Α

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

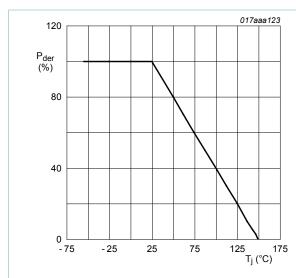


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

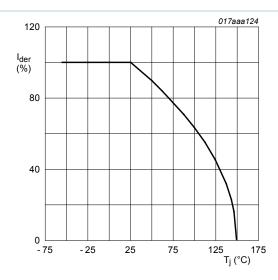


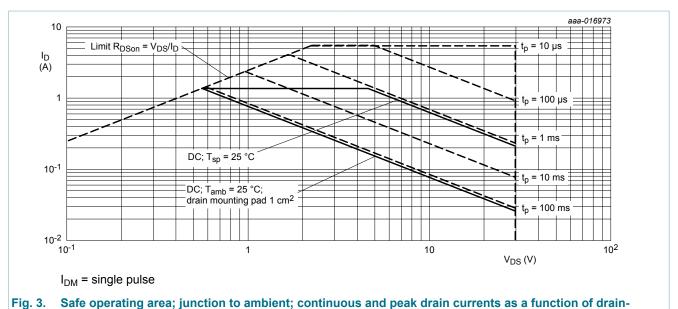
Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	315	360	K/W
			[2]	-	145	165	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	17	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

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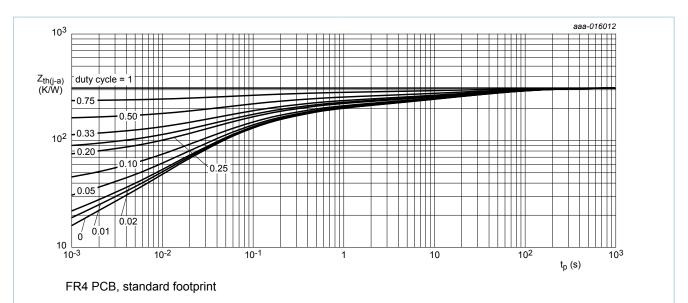
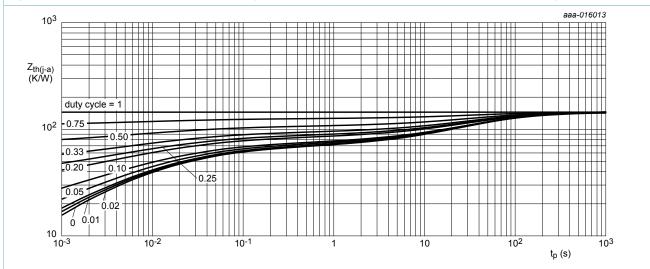


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.45	0.7	0.95	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μΑ
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μA
		$V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μA
		$V_{GS} = 2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		V_{GS} = -2.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 1.4 \text{ A}; T_j = 25 \text{ °C}$	-	210	250	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 1.4 \text{ A}; T_j = 150 \text{ °C}$	-	347	410	mΩ
		V_{GS} = 2.5 V; I_D = 1.2 A; T_j = 25 °C	-	240	310	mΩ
		$V_{GS} = 1.8 \text{ V}; I_D = 1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	270	380	mΩ
		$V_{GS} = 1.5 \text{ V}; I_D = 0.01 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	300	490	mΩ
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 1 A; T _j = 25 °C	-	4.1	-	S
Dynamic cl	naracteristics					<u>'</u>
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 1.5 A; V _{GS} = 4.5 V;	-	1.6	2.7	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.4	-	nC
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	89	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	11	-	pF
C _{rss}	reverse transfer capacitance		-	9	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; I_D = 0.8 A; V_{GS} = 4.5 V;	-	5	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	10	-	ns
$t_{d(off)}$	turn-off delay time		-	17	-	ns
t _f	fall time		-	3	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	$I_S = 0.7 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.86	1.2	V

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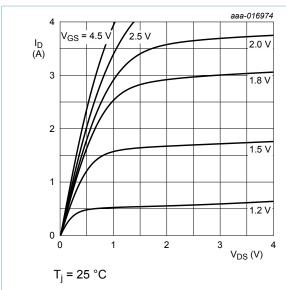
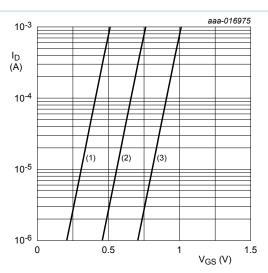


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

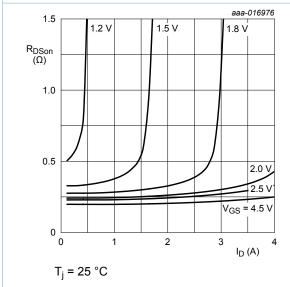


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

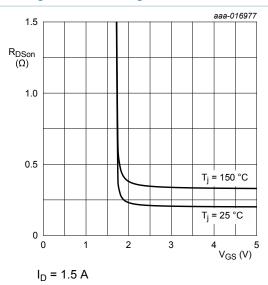


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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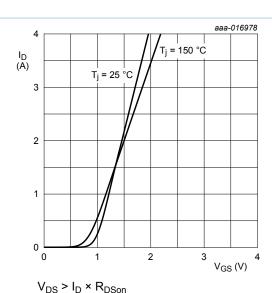


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

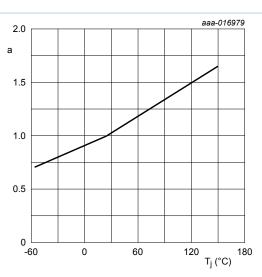
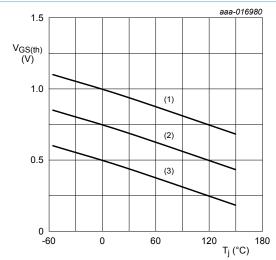


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

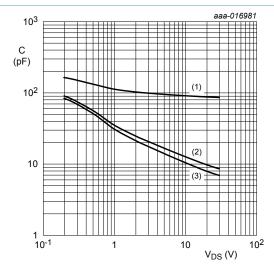
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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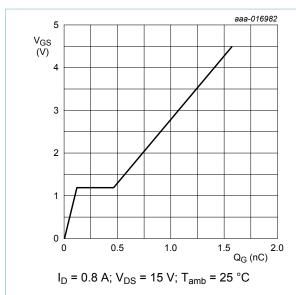


Fig. 14. Gate-source voltage as a function of gate charge; typical values

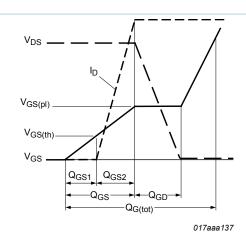


Fig. 15. MOSFET transistor: Gate charge waveform definitions

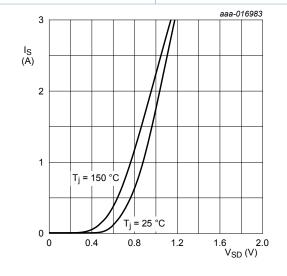
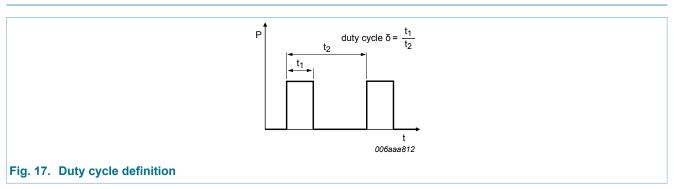


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$

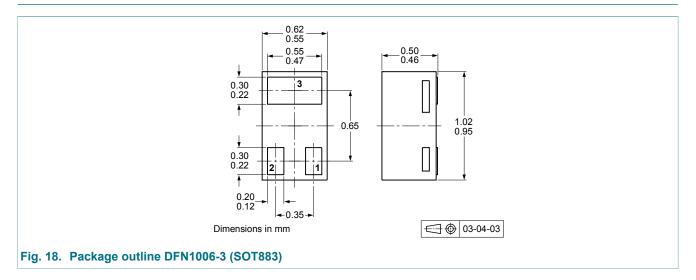


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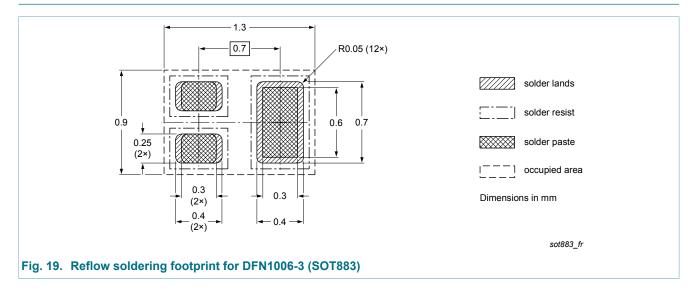
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12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZ200UNE v.1	20150312	Product data sheet	-	-

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15. Legal information

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